

# **General Description**

The AAT8343 is a low threshold P-channel MOS-FET designed for the battery, cell phone, and PDA markets. Using AnalogicTech's ultra-high-density proprietary TrenchDMOS™ technology, this product demonstrates high power handling and small size.

# **Applications**

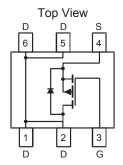
- **Battery Packs**
- Battery-Powered Portable Equipment
- Cellular and Cordless Telephones

## **Features**

- Drain-Source Voltage (max): -20V
- Continuous Drain Current<sup>1</sup> (max): -4.5A @ 25°C
- Low On-Resistance:

  - 60mΩ @ V<sub>GS</sub> = -4.5V 110mΩ @ V<sub>GS</sub> = -2.5V

# **TSOP-6 Package**



## **Absolute Maximum Ratings**

 $T_A = 25$ °C, unless otherwise noted.

Symbol	Description		Value	Units	
$V_{DS}$	Drain-Source Voltage		-20	V	
$V_{GS}$	Gate-Source Voltage		±12	V	
ı	Continuous Drain Current @ T <sub>J</sub> = 150°C¹	$T_A = 25^{\circ}C$	±4.5		
I <sub>D</sub>		T <sub>A</sub> = 70°C	±3.6	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>		±16	A	
I <sub>S</sub>	Continuous Source Current (Source-Drain Diode)1	-1.3			
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C		
T <sub>STG</sub>	Storage Temperature Range		-55 to 150	°C	

## Thermal Characteristics<sup>1</sup>

Symbol	Description		Тур	Max	Units	
$R_{\theta JA}$	Junction-to-Ambient Steady State		95	115	°C/W	
$R_{\theta JA2}$	Junction-to-Ambient t<5 Seconds		51	62	°C/W	
$R_{\theta JF}$	Junction-to-Foot		25	30	°C/W	
P <sub>D</sub>	Maximum Power Dissipation	T <sub>A</sub> = 25°C		2.0	W	
		T <sub>A</sub> = 70°C		1.3	VV	

<sup>1.</sup> Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 5-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications.  $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$  where the foot thermal reference is defined as the normal solder mounting surface of the device's leads. R<sub>θJF</sub> is guaranteed by design; however, R<sub>eCA</sub> is determined by the PCB design. Actual maximum continuous current is limited by the application's design.

<sup>2.</sup> Pulse test: Pulse Width = 300µs.



## **Electrical Characteristics**

 $T_{J}$  = 25°C, unless otherwise noted.

Symbol	Description	Conditions	Min	Тур	Max	Units	
DC Characteristics							
BV <sub>DSS</sub>	Drain-Source Breakdown	$V_{GS} = 0V, I_{D} = -250\mu A$	-20			V	
	Voltage						
В	Drain-Source On-Resistance <sup>1</sup>	$V_{GS} = -4.5V, I_D = -4.5A$		49	60	) mΩ	
R <sub>DS(ON)</sub>		$V_{GS} = -2.5V, I_D = -3.3A$		85	110	11152	
I <sub>D(ON)</sub>	On-State Drain Current <sup>1</sup>	$V_{GS}$ = -4.5V, $V_{DS}$ = -5V (pulsed)	-16			Α	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-0.6			V	
I <sub>GSS</sub>	Gate-Body Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$			±100	nA	
I <sub>DSS</sub>	Drain Source Leakage Current	$V_{GS} = 0V$ , $V_{DS} = -20V$			-1		
		$V_{GS} = 0V, V_{DS} = -16V, T_{J} = 70^{\circ}C^{2}$			-5 μA		
9 <sub>fs</sub>	Forward Transconductance <sup>1</sup>	$V_{DS} = -5V, I_{D} = -4.5A$		7		S	
Dynamic Characteristics <sup>2</sup>							
$Q_G$	Total Gate Charge	$V_{DS}$ = -10V, $R_{D}$ = 2.2 $\Omega$ , $V_{GS}$ = -4.5V		8.5			
$Q_{GS}$	Gate-Source Charge	$V_{DS} = -10V$ , $R_{D} = 2.2\Omega$ , $V_{GS} = -4.5V$		1.8		nC	
$Q_{GD}$	Gate-Drain Charge	$V_{DS}$ = -10V, $R_{D}$ = 2.2 $\Omega$ , $V_{GS}$ = -4.5V		2.9			
t <sub>D(ON)</sub>	Turn-On Delay	$V_{DS} = -10V$ , $R_D = 2.2\Omega$ , $V_{GS} = -4.5V$ , $R_G = 6\Omega$		12			
t <sub>R</sub>	Turn-On Rise Time	$V_{DS} = -10V$ , $R_D = 2.2\Omega$ , $V_{GS} = -4.5V$ , $R_G = 6\Omega$		32		no	
t <sub>D(OFF)</sub>	Turn-Off Delay	$V_{DS}$ = -10V, $R_{D}$ = 2.2 $\Omega$ , $V_{GS}$ = -4.5V, $R_{G}$ = 6 $\Omega$		64		ns	
t <sub>F</sub>	Turn-Off Fall Time	$V_{DS} = -10V$ , $R_{D} = 2.2\Omega$ , $V_{GS} = -4.5V$ , $R_{G} = 6\Omega$		40			
Source-Drain Diode Characteristics							
V <sub>SD</sub>	Source-Drain Forward	$V_{GS} = 0$ , $I_S = -4.5A$			-1.3	V	
	Voltage <sup>1</sup>						
I <sub>s</sub>	Continuous Diode Current <sup>3</sup>				-1.3	Α	

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<sup>1.</sup> Pulse test: Pulse Width = 300µs.

<sup>2.</sup> Guaranteed by design. Not subject to production testing.

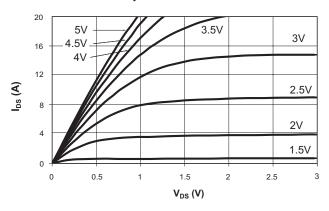
<sup>3.</sup> Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 5-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications.  $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$  where the foot thermal reference is defined as the normal solder mounting surface of the device's leads.  $R_{\theta JF}$  is guaranteed by design; however,  $R_{\theta CA}$  is determined by the PCB design. Actual maximum continuous current is limited by the application's design.



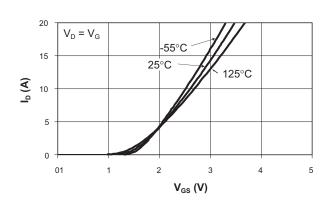
# **Typical Characteristics**

 $T_{\perp}$  = 25°C, unless otherwise noted.

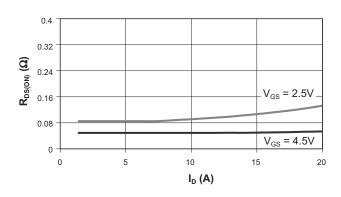
### **Output Characteristics**



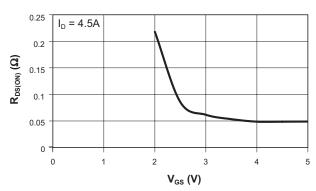
#### **Transfer Characteristics**



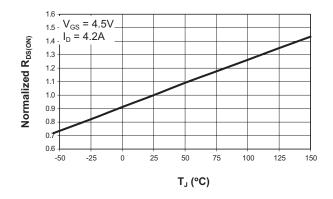
**On-Resistance vs. Drain Current** 



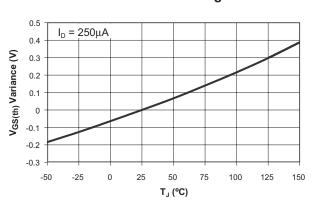
On-Resistance vs. Gate-to-Source Voltage



**On-Resistance vs. Junction Temperature** 



**Threshold Voltage** 

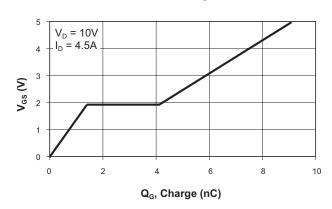




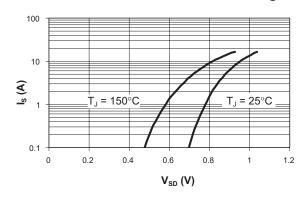
# **Typical Characteristics**

 $T_{\perp}$  = 25°C, unless otherwise noted.

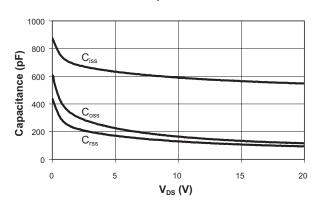
### **Gate Charge**



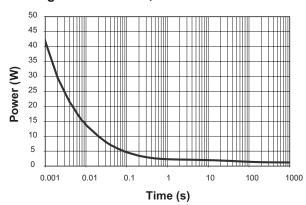
#### Source-Drain Diode Forward Voltage



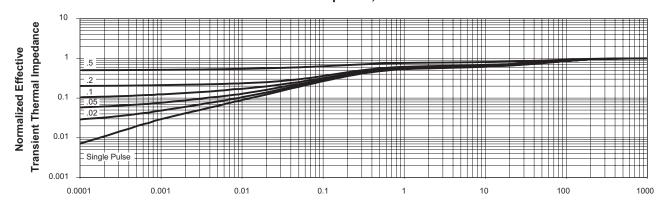
#### Capacitance



### Single Pulse Power, Junction to Ambient



#### **Transient Thermal Response, Junction to Ambient**



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# **Ordering Information**

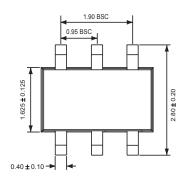
Package	Marking <sup>1</sup>	Part Number (Tape and Reel) <sup>2</sup>
TSOP-6	KEXYY	AAT8343IDU-T1



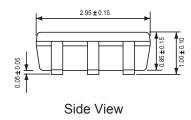
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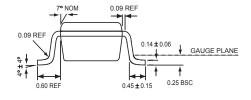
## **Package Information**

#### TSOP-6



Top View





**End View** 

All dimensions in millimeters.

<sup>1.</sup> XYY = assembly and date code.

<sup>2.</sup> Sample stock is generally held on part numbers listed in BOLD.



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